

Publikacje w czasopismach

1. Kudrawiec R., Latkowska M., **Baranowski M.**, Misiewicz J., Li L.H., and Harmand J.C., 2013, *Photoreflectance, photoluminescence, and microphotoluminescence study of optical transitions between delocalized and localized states in GaN_{0.02}As_{0.98}, Ga_{0.95}In_{0.05}N_{0.02}As_{0.98}, and GaN_{0.02}As_{0.90}Sb_{0.08} layers*, Phys. Rev. B **88**, 125201
2. Zhang L., Lieten R.R, Latkowska M., **Baranowski M.**, Kudrawiec R., Cheng K., Liang H., and Borgh G., 2013, *Design and Optical Characterization of Novel InGaN/GaN Multiple Quantum Well Structures by Metal Organic Vapor Phase Epitaxy*, Jpn. J. Appl. Phys., **52**, 08JL10
3. **Baranowski M.**, Kudrawiec R., and Misiewicz J., 2013, *Theoretical Studies of the Influence of Temperature on Photoluminescence Dynamics in GalnNAs/GaAs Quantum Wells*, Jpn. J. Appl. Phys. **52** 08JL04
4. Syperek M., **Baranowski M.**, Sęk G., Misiewicz J., Löffler A., Höfling S., Reitzenstein S., Kamp M., and Forchel A., 2013 *Impact of wetting-layer density of states on the carrier relaxation process in low indium content self-assembled (In,Ga)As/GaAs quantum dots* Phys. Rev. B **87**, 125305
5. **Baranowski M.**, Kudrawiec R., Latkowska M., Syperek M., Misiewicz J., Sarmiento T. and Harris J.S. 2013, *Enhancement of photoluminescence from GalnNAsSb quantum wells upon annealing: Improvement of material quality and carrier collection by the quantum well* J. Phys.: Condens. Matter, **25**, 065801
6. Reisfeld R., Levchenko V., Saraidarov T., Rysiakiewicz-Pasek E., **Baranowski M.**, Podhorodecki A., Misiewicz J., Antropova T., 2012 *Steady state and femtosecond spectroscopy of Perylimide Red dye in porous and sol-gel glasses*, Chemical Physics Letters, **546**, 171
7. **Baranowski M.**, Latkowska M., Kudrawiec R., Syperek M., Misiewicz J., Giri Sadasivam K., Shim J. and Lee J.K., 2012, *Time-resolved photoluminescence studies of the optical quality of InGaN/GaN multi-quantum well grown by MOCVD—antimony surfactant effect* Semicond. Sci. Technol., **27**, 105027.
8. **Baranowski M.**, Kudrawiec R., Latkowska M., Syperek M., Misiewicz J., and Gupta J.A., 2012, *Dynamics of localized excitons in Ga_{0.69}In_{0.31}N_{0.015}As_{0.985}/GaAs quantum well: Experimental studies and Monte-Carlo simulations* , Appl. Phys. Lett., **100**, 202105.
9. **Baranowski M.**, Syperek M., Kudrawiec R., Misiewicz J., Gupta J.A., Wu X., and Wang R., 2012, *Carrier dynamics in type-II GaAsSb/GaAs quantum well*, J. Phys.: Condens. Matter, **24**, 185801.
10. **Baranowski M.**, Latkowska M., Kudrawiec R., Misiewicz J., 2011, *Model of hopping excitons in GalnNAs: Simulations of sharp lines in micro- photoluminescence spectra and their dependence on the excitation power and temperature*, J. Phys.: Condens. Matter, **23**, 205804.
11. **Baranowski M.**, Kudrawiec R., Syperek M., Misiewicz J., Zhao H., Sadeghi M. and Wang S.M. 2011 *Contactless electroreflectance, photoluminescence and time-resolved photoluminescence of GalnNAs quantum wells obtained by the MBE method with N-irradiation*, Semicond. Sci. Technol., **26**, 045012,
12. **Baranowski M.**, Syperek M., Kudrawiec R., Misiewicz J., Gupta J.A., Wu X., and Wang R., 2011, *Carrier dynamics between delocalized and localized states in type-II GaAsSb/GaAs quantum wells*, Appl. Phys. Lett. **98**, 061910,

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Prace pokonferencyjne i doniesienia zjazdowe

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2. **Baranowski M.**, Latkowska M., Kudrawiec R. and Misiewicz J., 2011, *Hopping excitons in GaInNAs - Simulation of micro-and macro-photoluminescence spectra*, Acta Physica Polonica A **120**, 899.